Single P-channel MOSFET

ELM32411LA-S

■General description

ELM32411LA-S uses advanced trench technology to provide excellent Rds(on), low gate charge and low gate resistance.

■Features

- Vds=-55V
- Id=-7A
- Rds(on) < 80mΩ (Vgs=-10V)
- Rds(on) < 150mΩ (Vgs=-4.5V)

■Maximum absolute ratings

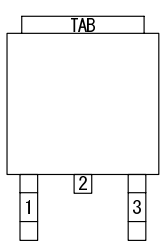
Parameter		Symbol	Limit	Unit	Note
Drain-source voltage		Vds	-55	V	
Gate-source voltage		Vgs	±20	V	
Continuous drain current	Ta=25℃	Id	-7	A	
	Ta=70℃		-6		
Pulsed drain current		Idm	-30	A	3
Power dissipation	Ta=25℃	Pd	28	W	
	Ta=70℃		18		
Junction and storage temperature range		Tj, Tstg	-55 to 150	℃	

■Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-case	Steady-state	Rθjc		3	℃/W	
Maximum junction-to-ambient	Steady-state	Rθja		75	℃/W	

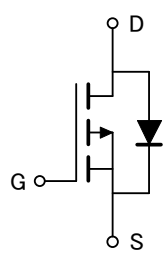
■Pin configuration

TO-252-3 (TOP VIEW)



Pin No.	Pin name
1	GATE
2	DRAIN
3	SOURCE

■Circuit



■Electrical characteristics

Ta=25℃

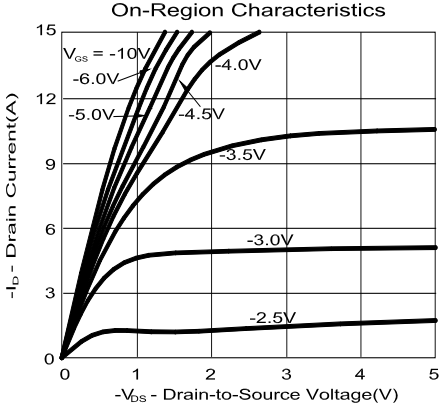
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BVdss	Id=−250μA, Vgs=0V	−55			V	
Zero gate voltage drain current	Idss	Vds=−44V, Vgs=0V			−1	μA	
		Vds=−36V, Vgs=0V, Tj=125℃			−10		
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V			±250	nA	
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=−250μA	−1.0	−1.5	−2.5	V	
On state drain current	Id(on)	Vgs=−10V, Vds=−5V	−32			A	1
Static drain-source on-resistance	Rds(on)	Vgs=−10V, Id=−7A		60	80	mΩ	1
		Vgs=−4.5V, Id=−6A		90	150	mΩ	
Forward transconductance	Gfs	Vds=−10V, Id=−7A		9		S	1
Diode forward voltage	Vsd	Is=If, Vgs=0V			−1	V	1
Max. body-diode continuous current	Is				−1.3	A	
Pulsed body-diode current	Ism				−2.6	A	3
DYNAMIC PARAMETERS							
Input capacitance	Ciss	Vgs=0V, Vds=−30V, f=1MHz		760		pF	
Output capacitance	Coss			90		pF	
Reverse transfer capacitance	Crss			40		pF	
SWITCHING PARAMETERS							
Total gate charge	Qg	Vgs=−10V, Vds=−27.5V Id=−7A		15.0		nC	2
Gate-source charge	Qgs			2.5		nC	2
Gate-drain charge	Qgd			3.0		nC	2
Turn-on delay time	td(on)	Vgs=−10V, Vds=−20V Id≅−1A, Rl=1Ω, Rgen=6Ω		7	14	ns	2
Turn-on rise time	tr			10	20	ns	2
Turn-off delay time	td(off)			19	34	ns	2
Turn-off fall time	tf			12	22	ns	2
Body diode reverse recovery time	trr	If=−7A, dI/dt=100A/μs		15.5		ns	
Body diode reverse recovery charge	Qrr			7.9		nC	

NOTE :

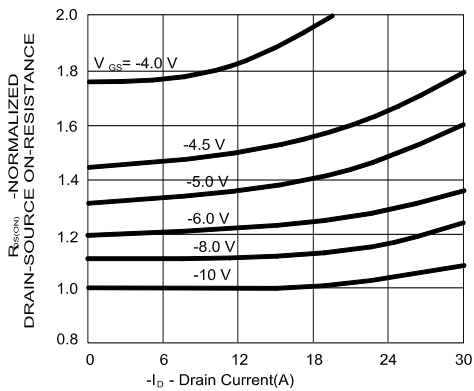
1. Pulse test : Pulsed width ≤ 300μsec and Duty cycle ≤ 2%.
2. Independent of operating temperature.
3. Pulsed width limited by maximum junction temperature.

■Typical electrical and thermal characteristics

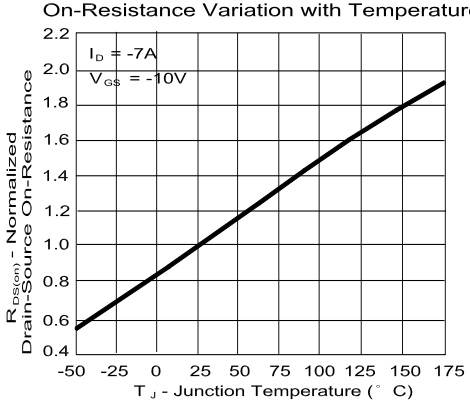
On-Region Characteristics



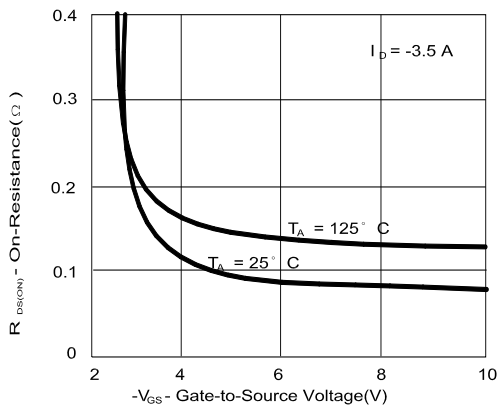
On-Resistance Variation with Drain Current and Gate Voltage



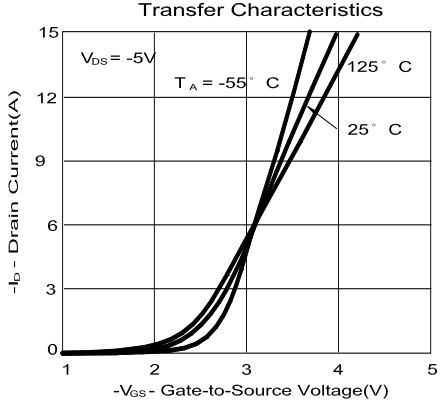
On-Resistance Variation with Temperature



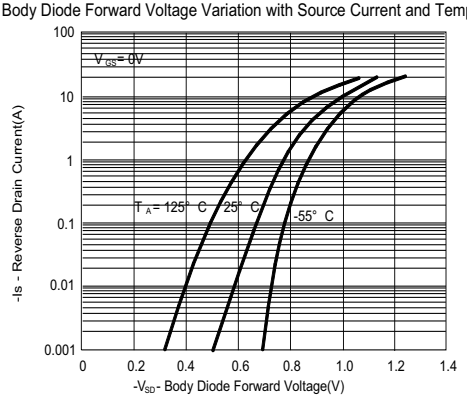
On-Resistance Variation with Gate-to-Source Voltage



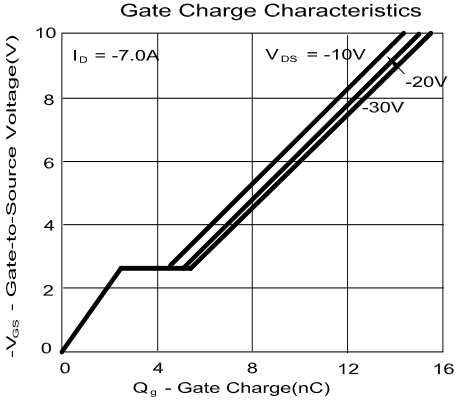
Transfer Characteristics



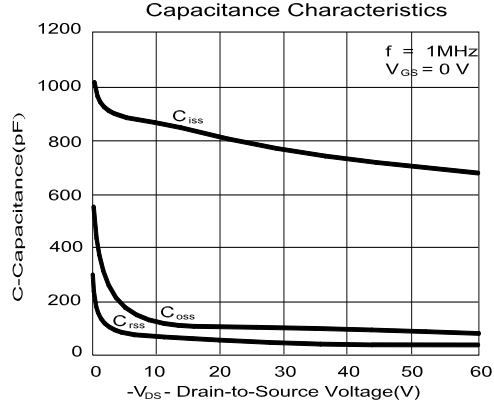
Body Diode Forward Voltage Variation with Source Current and Temperature



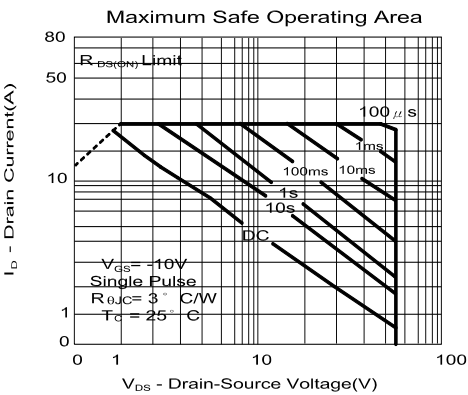
Gate Charge Characteristics



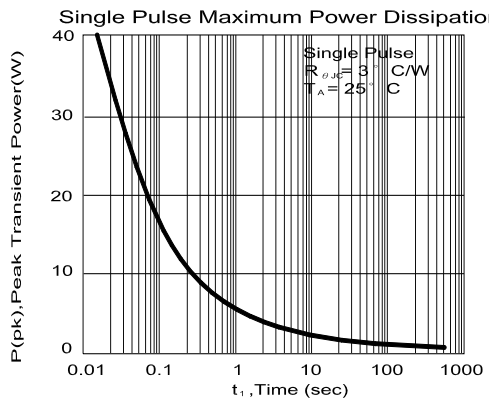
Capacitance Characteristics



Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

